

# **Zero Recovery Silicon Carbide Schottky Diode**

## **PRODUCT APPLICATIONS**

- Anti-Parallel Diode

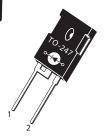
   Switchmode Power Supply
   Inverters
- Power Factor Correction (PFC)

#### **PRODUCT FEATURES**

- Zero Recovery Times (t<sub>rr</sub>)
- Popular TO-247 Package
- · Low Forward Voltage
- Low Leakage Current

## **PRODUCT BENEFITS**

- · Higher Reliability Systems
- Minimizes or eliminates snubber





1 - Cathode 2 - Anode Back of Case - Cathode

## **MAXIMUM RATINGS**

All Ratings: T<sub>C</sub> = 25°C unless otherwise specified.

| Symbol                            | Characteristic / Test Conditions   |                        | Ratings    | Unit  |  |
|-----------------------------------|--|------------------------|------------|-------|--|
| V <sub>R</sub>                    | Maximum D.C. Reverse Voltage   |                        |            |       |  |
| V <sub>RRM</sub>                  | Maximum Peak Repetitive Reverse Voltage                                  |                        | 1700       | Volts |  |
| V <sub>RWM</sub>                  | Maximum Working Peak Reverse Voltage                                     |                        |            |       |  |
| I <sub>F</sub>                    | Maximum D.C. Forward Current   | T <sub>C</sub> = 25°C  | 23         |       |  |
|                                   |  | T <sub>C</sub> = 110°C | 15         | A     |  |
| I <sub>FSM</sub>                  | Non-Repetitive Forward Surge Current ( t <sub>p</sub> = 10ms, Half Sine) | T <sub>C</sub> = 25°C  | 55         | Amps  |  |
|                                   |  | T <sub>C</sub> = 110°C | 50         |       |  |
| P <sub>tot</sub>                  | Power Dissipation  | T <sub>C</sub> = 25°C  | 214        | ١٨/   |  |
|                                   |  | T <sub>c</sub> = 110°C | 92         | W     |  |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Junction Temperature Range                         |                        | -55 to 175 | - °C  |  |
| T <sub>L</sub>                    | ad Temperature for 10 Seconds  |                        | 300        |       |  |

### STATIC ELECTRICAL CHARACTERISTICS

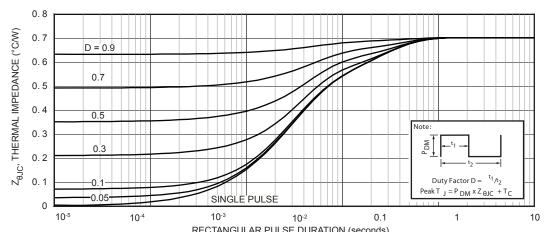
| Symbol          | Characteristic / Test Conditions   |  | Min | Тур  | Max | Unit  |
|-----------------|--|--|-----|------|-----|-------|
| V <sub>F</sub>  | Forward Voltage  | I <sub>F</sub> = 10A T <sub>J</sub> = 25°C     |     | 1.5  | 1.8 | Volts |
|                 |  | I <sub>F</sub> = 10A, T <sub>J</sub> = 175°C   |     | 2.25 |     |       |
| I <sub>RM</sub> | Maximum Reverse Leakage Current  | V <sub>R</sub> = 1700V T <sub>J</sub> = 25°C   |     | 10   | 200 | μА    |
|                 |  | V <sub>R</sub> = 1700V, T <sub>J</sub> = 175°C |     | 500  |     |       |
| Q <sub>c</sub>  | Total Capactive Charge $V_R$ = 800V, $I_F$ = 10A, di/dt = -500A/ $\mu$ s, $T_J$ = 25°C |  |     | 88   |     | nC    |
| C <sub>T</sub>  | Junction Capacitance V <sub>R</sub> = 0V, T <sub>J</sub> = 25°C, f = 1MHz              |  |     | 1120 |     | pF    |
|                 | Junction Capacitance V <sub>R</sub> = 300V, T <sub>J</sub> = 25°C, f = 1MHz            |  |     | 93   |     |       |
|                 | Junction Capacitance V <sub>R</sub> = 600V, T <sub>J</sub> = 25°C, f = 1MHz            |  |     | 68   |     |       |

#### THERMAL AND MECHANICAL CHARACTERISTICS

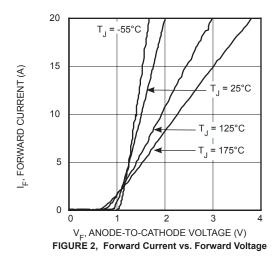
| Symbol           | Characteristic / Test Conditions    | Min | Тур  | Max | Unit  |
|------------------|-------------------------------------|-----|------|-----|-------|
| R <sub>eJC</sub> | Junction-to-Case Thermal Resistance |     |      | 0.7 | °C/W  |
| W <sub>T</sub>   | Package Weight                      |     | 0.22 |     | OZ    |
|                  |                                     |     | 5.9  |     | g     |
| Torque           | Maximum Mounting Torque             |     |      | 10  | lb∙in |
|                  |                                     |     |      | 1.1 | N·m   |

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## **TYPICAL PERFORMANCE CURVES**



RECTANGULAR PULSE DURATION (seconds)
FIGURE 1. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION



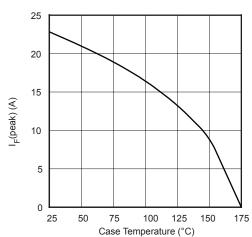


FIGURE 3, Maximum Forward Current vs. Case Temperature

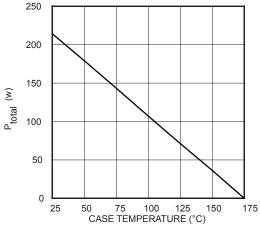
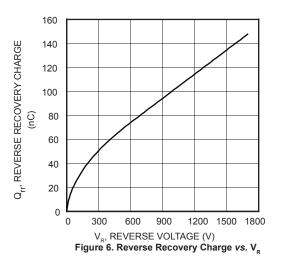


Figure 4. Maximum Power Dissipation vs. Case Temperature



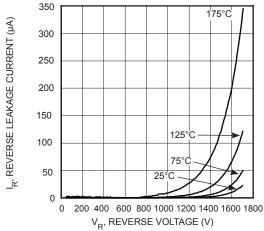
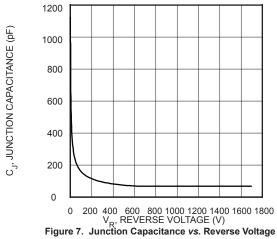
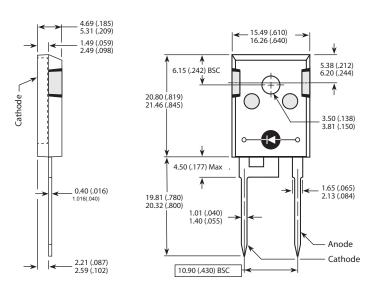


Figure 5. Reverse Leakage Currents vs. Reverse Voltage



## **TO-247 Package Outline**



Dimensions in Millimeters and (Inches)

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